



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



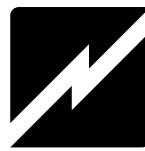
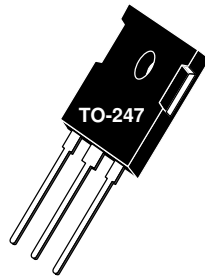
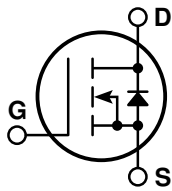
Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China





**ADVANCED
POWER
TECHNOLOGY®**

APT1001RBN 1000V 11.0A 1.00Ω

POWER MOS IV®

N-CHANNEL ENHANCEMENT MODE HIGH VOLTAGE POWER MOSFETS

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT 1001RBN		UNIT
V _{DSS}	Drain-Source Voltage	1000		Volts
I _D	Continuous Drain Current @ T _C = 25°C	11		Amps
I _{DM}	Pulsed Drain Current ①	44		
V _{GS}	Gate-Source Voltage	±30		Volts
P _D	Total Power Dissipation @ T _C = 25°C	310		Watts
	Linear Derating Factor	2.48		W/°C
T _J ,T _{STG}	Operating and Storage Junction Temperature Range	-55 to 150		°C
T _L	Lead Temperature: 0.063" from Case for 10 Sec.	300		

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 250 \mu A$)	APT1001RBN	1000		Volts
$I_{D(ON)}$	On State Drain Current ^② ($V_{DS} > I_{D(ON)} \times R_{DS(ON)} \text{ Max}, V_{GS} = 10V$)	APT1001RBN	11		Amps
$R_{DS(ON)}$	Drain-Source On-State Resistance ^② ($V_{GS} = 10V, 0.5 I_D [\text{Cont.}]$)	APT1001RBN		1.00	Ohms
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = V_{DSS}, V_{GS} = 0V$)			250	μA
	Zero Gate Voltage Drain Current ($V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$)			1000	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 30V, V_{DS} = 0V$)			± 100	nA
$V_{GS(TH)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 1.0mA$)	2		4	Volts

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.40	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction to Ambient			40	



CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

USA

405 S.W. Columbia Street

EUROPE

Avenue J.F. Kennedy Bât B4 Parc Cadéra Nord

Bend, Oregon 97702-1035

F-33700 Merignac - France

Phone: (541) 382-8028

Phone: (33) 5 57 92 15 15

FAX: (541) 388-0364

FAX: (33) 5 56 47 97 61

DYNAMIC CHARACTERISTICS

APT1001RBN

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1 \text{ MHz}$		2460	2950	pF
C_{oss}	Output Capacitance			360	500	
C_{rss}	Reverse Transfer Capacitance			105	160	
Q_g	Total Gate Charge ③	$V_{GS} = 10V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$		90	130	nC
Q_{gs}	Gate-Source Charge			9.3	14	
Q_{gd}	Gate-Drain ("Miller") Charge			47	70	
$t_d(\text{on})$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$ $R_G = 1.8\Omega$		15	30	ns
t_r	Rise Time			16	32	
$t_d(\text{off})$	Turn-off Delay Time			64	95	
t_f	Fall Time			24	48	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number	MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)	APT1001RBN		11	Amps
I_{SM}	Pulsed Source Current ① (Body Diode)	APT1001RBN		44	Amps
V_{SD}	Diode Forward Voltage ② ($V_{GS} = 0V$, $I_S = -I_D [\text{Cont.}]$)			1.3	Volts
t_{rr}	Reverse Recovery Time ($I_S = -I_D [\text{Cont.}]$, $dI_S/dt = 100A/\mu s$)		636	1200	ns
Q_{rr}	Reverse Recovery Charge ($I_S = -I_D [\text{Cont.}]$, $dI_S/dt = 100A/\mu s$)		4.5	11	μC

SAFE OPERATING AREA CHARACTERISTICS

Symbol	Characteristic	Test Conditions / Part Number	MIN	TYP	MAX	UNIT
SOA1	Safe Operating Area	$V_{DS} = 0.4 V_{DSS}$, $I_{DS} = P_D / 0.4 V_{DSS}$, $t = 1 \text{ Sec.}$	310			Watts
SOA2	Safe Operating Area	$I_{DS} = I_D [\text{Cont.}]$, $V_{DS} = P_D / I_D [\text{Cont.}]$, $t = 1 \text{ Sec.}$	310			
I_{LM}	Inductive Current Clamped	APT1001RBN	44			Amps

① Repetitive Rating: Pulse width limited by maximum junction temperature. See Transient Thermal Impedance Curve. (Fig.1)

② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

APT Reserves the right to change, without notice, the specifications and information contained herein.

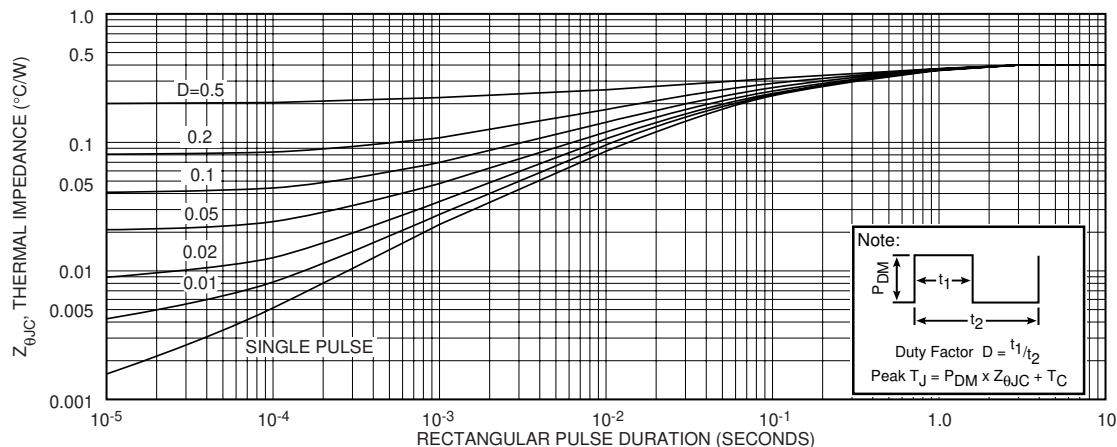


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

APT1001RBN

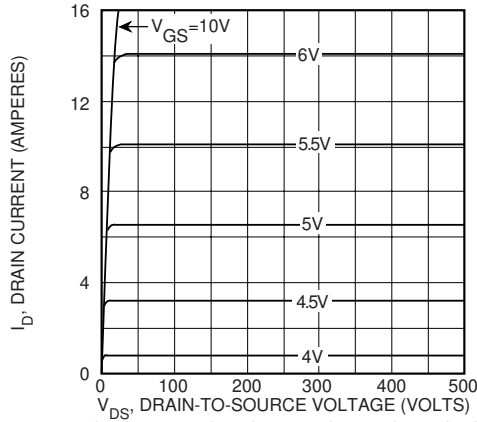


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

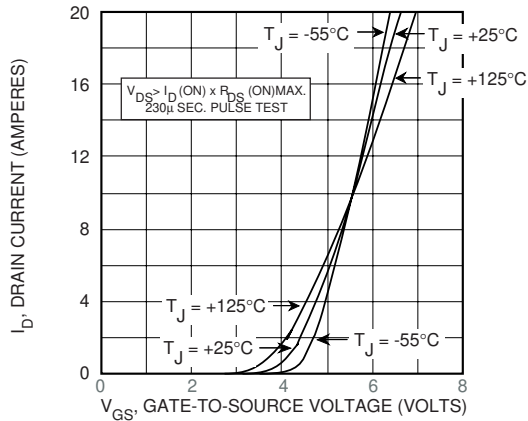


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

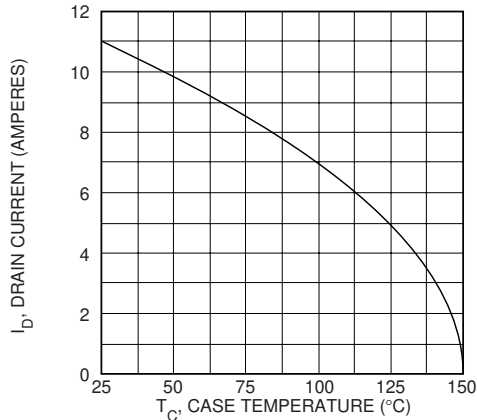


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

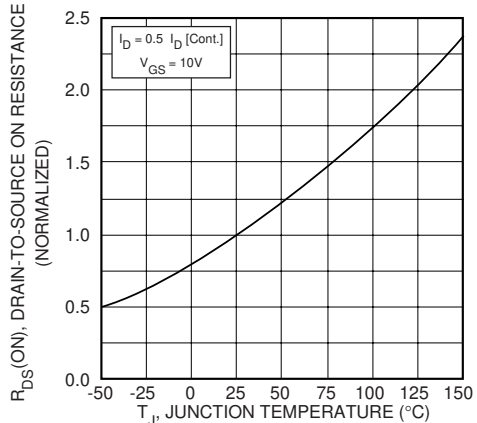


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

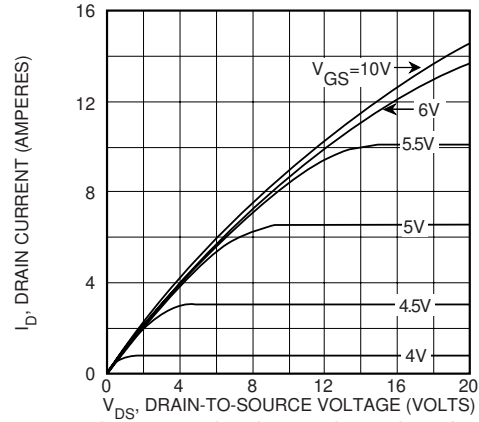


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

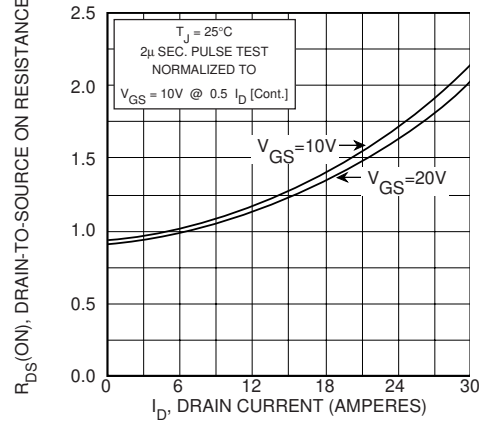


FIGURE 5, $R_{DS(ON)}$ vs DRAIN CURRENT

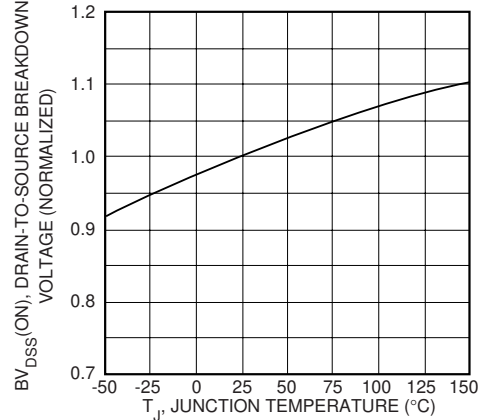


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

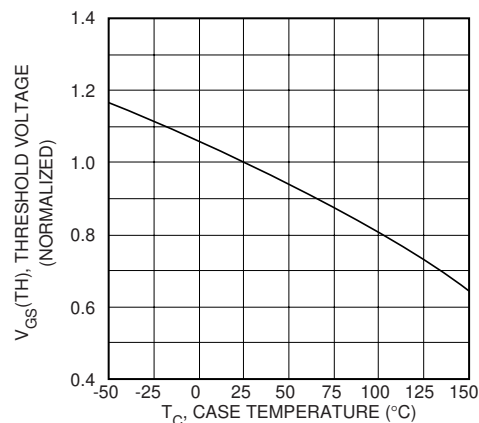


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

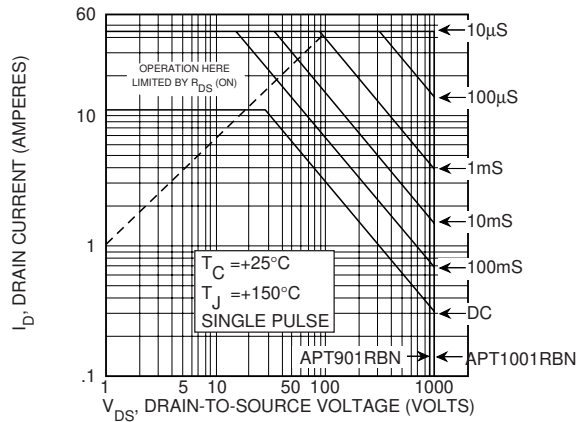


FIGURE 10, MAXIMUM SAFE OPERATING AREA

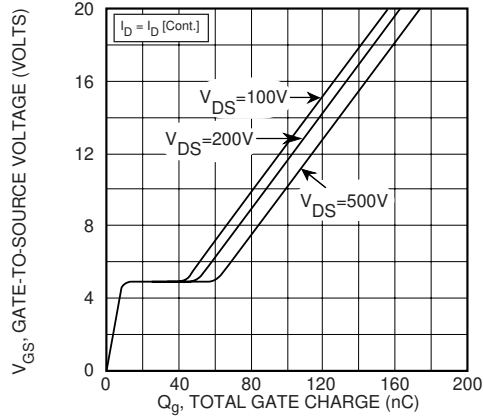


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

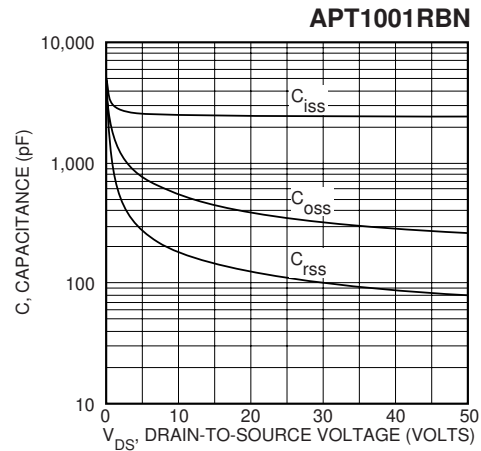


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

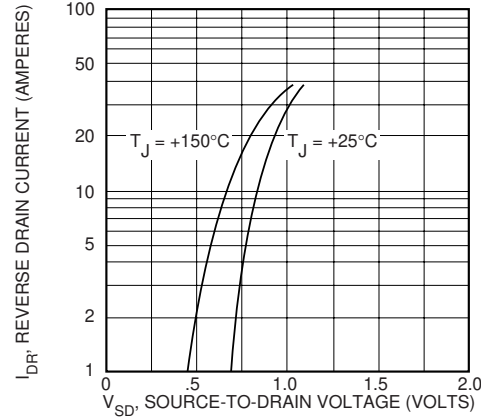
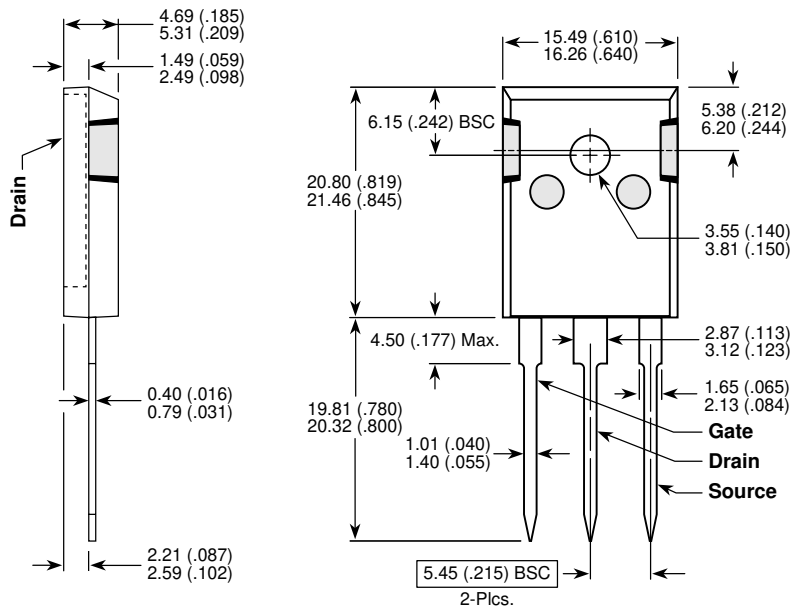


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

TO-247AD Package Outline



Dimensions in Millimeters and (Inches)